

MOSFET - N-Channel, SOT-23

300 mA, 20 V

MMBF0201NL,
MVMBF0201NL

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- MVMBF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb-Free and are RoHS Compliant

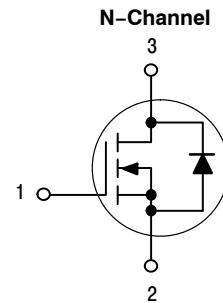
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	20	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	Vdc
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ – Continuous @ $T_A = 70^\circ\text{C}$ – Pulsed Drain Current ($t_p \leq 10 \mu\text{s}$)	I_D I_D I_{DM}	300 240 750	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	225	mW
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

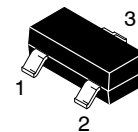
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

300 mAMPS – 20 VOLTS

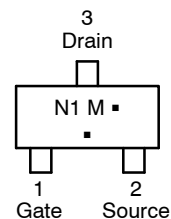
$R_{DS(on)} = 1 \Omega$



MARKING DIAGRAM AND PIN ASSIGNMENT



SOT-23
CASE 318
STYLE 21



N1 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBF0201NLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MVMBF0201NLT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBF0201NL, MVMBF0201NL

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 10\text{ }\mu\text{A}$)	$V_{(BR)DSS}$	20	–	–	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 16\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 16\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	I_{DSS}	– –	– –	1.0 10	μA dc
Gate-Body Leakage Current ($V_{GS} = \pm 20\text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	–	–	± 100	nA

ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$)	$V_{GS(th)}$	1.0	1.7	2.4	Vdc
Static Drain-to-Source On-Resistance ($V_{GS} = 10\text{ Vdc}$, $I_D = 300\text{ mA}$ dc) ($V_{GS} = 4.5\text{ Vdc}$, $I_D = 100\text{ mA}$ dc)	$r_{DS(on)}$	– –	0.75 1.0	1.0 1.4	Ω
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\text{ mA}$ dc)	g_{FS}	–	450	–	mMhos

DYNAMIC CHARACTERISTICS

Input Capacitance	($V_{DS} = 5.0\text{ V}$)	C_{iss}	–	45	–	pF
Output Capacitance	($V_{DS} = 5.0\text{ V}$)	C_{oss}	–	25	–	
Transfer Capacitance	($V_{DG} = 5.0\text{ V}$)	C_{rss}	–	5.0	–	

SWITCHING CHARACTERISTICS (Note 2)

Turn-On Delay Time	(V _{DD} = 15 Vdc, I _D = 300 mA, R _L = 50 Ω)	$t_{d(on)}$	–	2.5	–	ns
Rise Time		t_r	–	2.5	–	
Turn-Off Delay Time		$t_{d(off)}$	–	15	–	
Fall Time		t_f	–	0.8	–	
Gate Charge (See Figure 5)		Q_T	–	1400	–	pC

SOURCE-DrAIN DIODE CHARACTERISTICS

Continuous Current	I_S	–	–	0.3	A
Pulsed Current	I_{SM}	–	–	0.75	
Forward Voltage (Note 2)	V_{SD}	–	0.85	–	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.
2. Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS

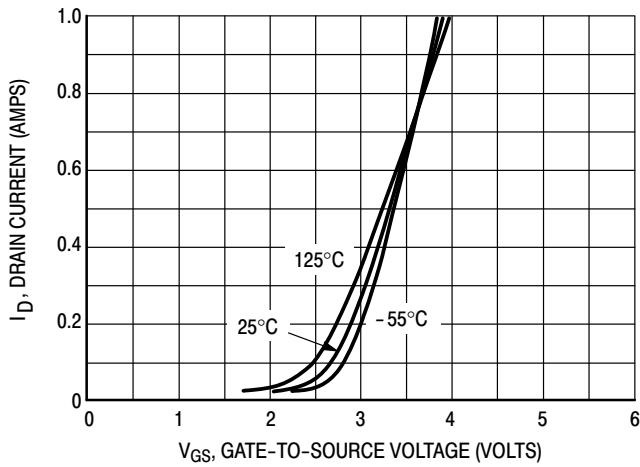


Figure 1. Transfer Characteristics

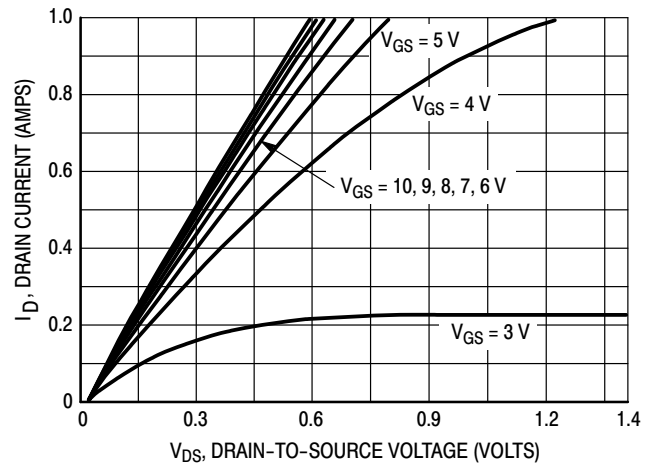


Figure 2. On-Region Characteristics

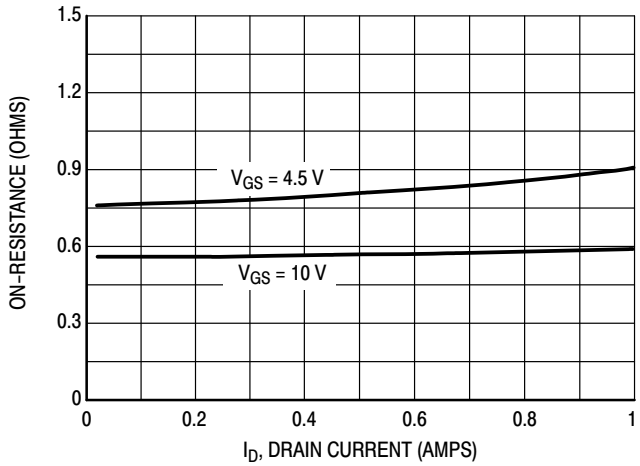


Figure 3. On-Resistance versus Drain Current

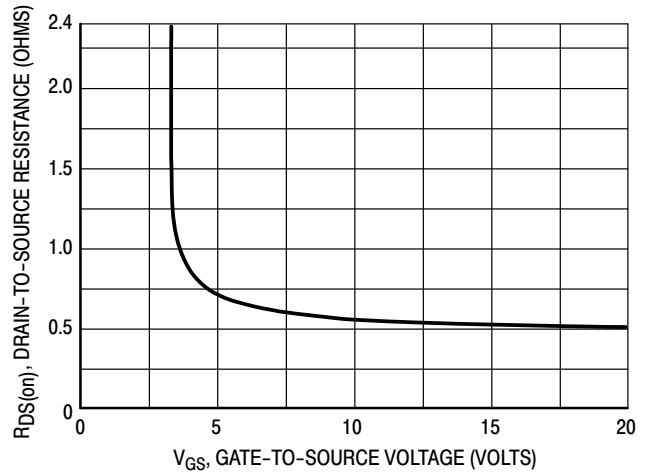


Figure 4. On-Resistance versus Gate-to-Source Voltage

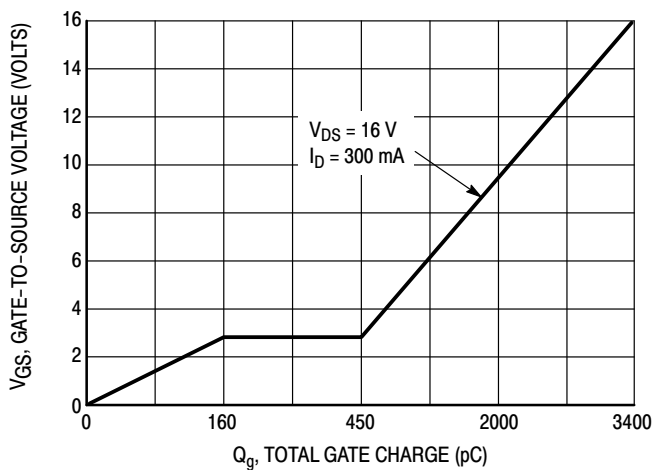


Figure 5. Gate Charge

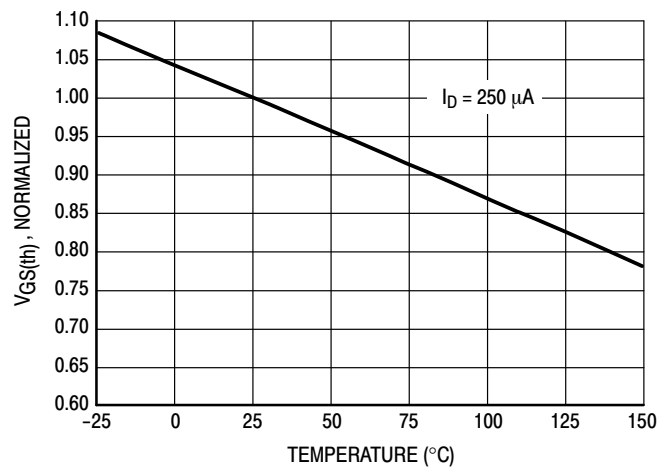


Figure 6. Threshold Voltage Variance Over Temperature

TYPICAL ELECTRICAL CHARACTERISTICS

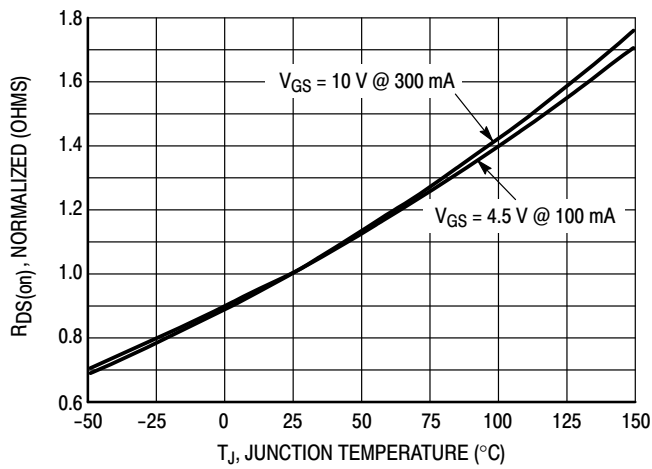


Figure 7. On-Resistance versus Junction Temperature

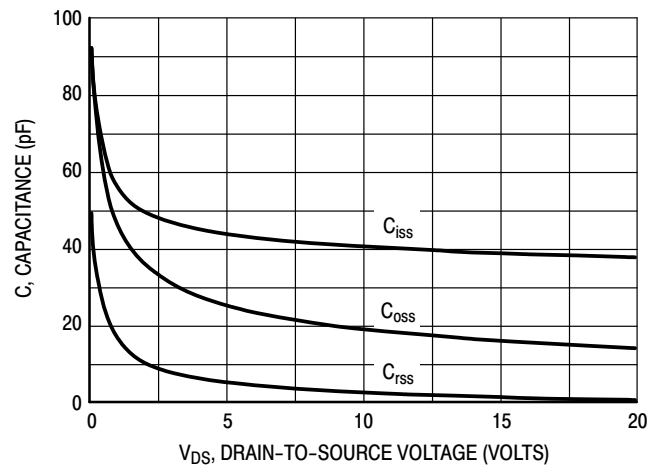


Figure 8. Capacitance

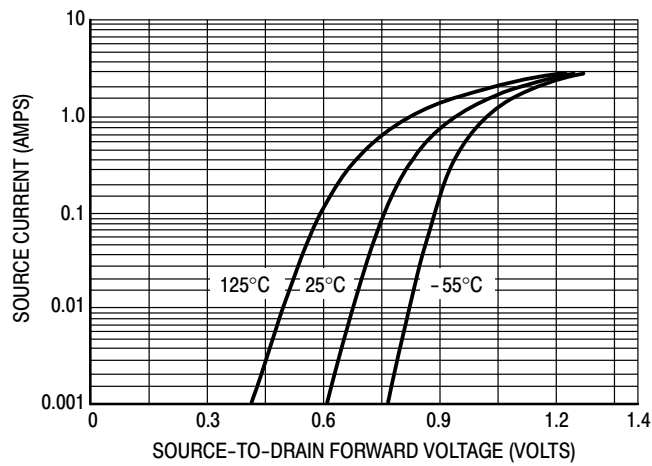


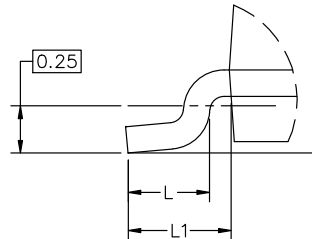
Figure 9. Source-to-Drain Forward Voltage versus Continuous Current (I_S)



SCALE 4:1

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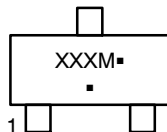


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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